

Vishay Siliconix

# Automotive N-Channel 100 V (D-S) 175 °C MOSFET

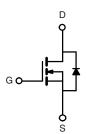
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	100				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.025				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.029				
I <sub>D</sub> (A)	40				
Configuration	Single				
Package	TO-252				



#### **FEATURES**

- TrenchFET<sup>®</sup> power MOSFET
- · Package with low thermal resistance
- 100 %  $\rm R_g$  and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_C = 25 \text{ °C}$ , unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V <sub>DS</sub>	100		
Gate-Source Voltage		V <sub>GS</sub>	± 20	V	
Continuous Drain Current	$T_C = 25 \ ^\circ C \ ^a$	Ŀ	40	A	
Continuous Drain Current	T <sub>C</sub> = 125 °C	. I <sub>D</sub>	26		
Continuous Source Current (Diode Conduction	n) <sup>a</sup>	I <sub>S</sub>	40		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	160		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	40		
Single Pulse Avalanche Energy	L = 0.1 IIIH	E <sub>AS</sub>	80	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	Pn	136	W	
	T <sub>C</sub> = 125 °C	гD	45	vv	
Operating Junction and Storage Temperature	Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	50	°C/W	
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.1	C/ VV	

Notes

a. Package limited.

b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$ 

c. When mounted on 1" square PCB (FR4 material).



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_D = 250 \mu A$		100	-	-	v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μΑ	1.5	-	2.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 100 V	-	-	1.0		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 100 V, T <sub>J</sub> = 125 °C	-	-	50	μA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 100 V, T <sub>J</sub> = 175 °C	-	-	250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	50	-	-	Α	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 40 A	-	0.019	0.025		
Drain Course On State Desistance a	Б	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 40 A, T <sub>J</sub> = 125 °C	-	-	0.050		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 V$	I <sub>D</sub> = 40 A, T <sub>J</sub> = 175 °C	-	-	0.063	Ω	
		$V_{GS} = 4.5 V$	I <sub>D</sub> = 20 A	-	0.021	0.029		
Forward Transconductance <sup>b</sup>	<b>g</b> fs	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 40 A		-	73	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>			-	2703	3380	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	312	390		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	127	160		
Total Gate Charge <sup>c</sup>	Qg			-	46	70		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 10 \text{ V}$	$V_{DS} = 50 \text{ V}, I_D = 40 \text{ A}$	-	8.2	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>			-	13	-	1	
Gate Resistance	Rg	f = 1 MHz		0.9	1.8	3.1	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>				11	17		
Rise Time <sup>c</sup>	t <sub>r</sub>	$\label{eq:VDD} \begin{array}{l} V_{DD}=50~V,~R_L=1.25~\Omega\\ I_D\cong40~A,~V_{GEN}=10~V,~R_g=1~\Omega \end{array}$		-	11	17	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	27	41		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	6	9		
Source-Drain Diode Ratings and Characteristics <sup>b</sup>								
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	160	Α	
Forward Voltage	V <sub>SD</sub>	$I_{\rm F} = 40 \text{ A}, V_{\rm GS} = 0 \text{ V}$		_	0.9	1.5	V	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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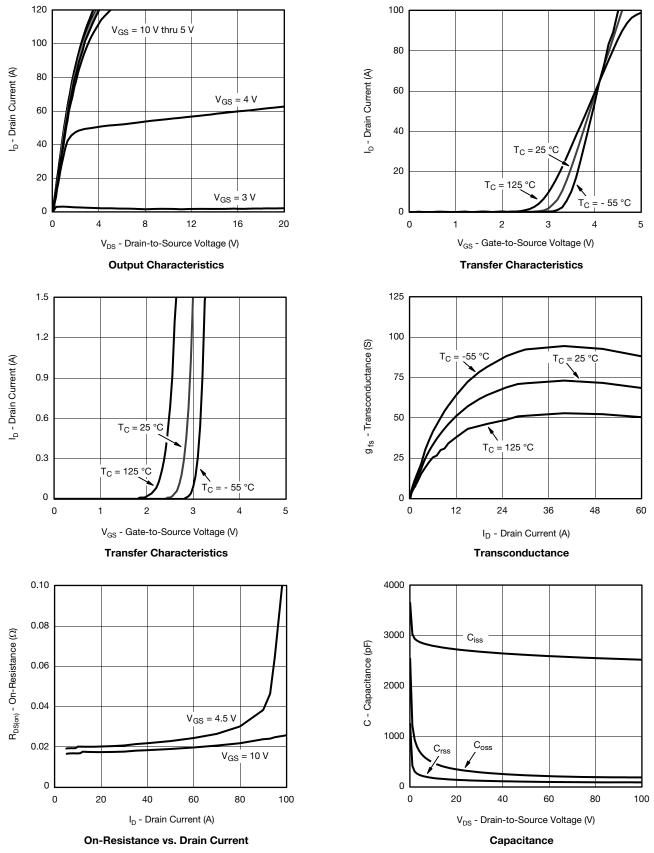
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SQD40N10-25

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### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



S15-1873-Rev. E, 10-Aug-15

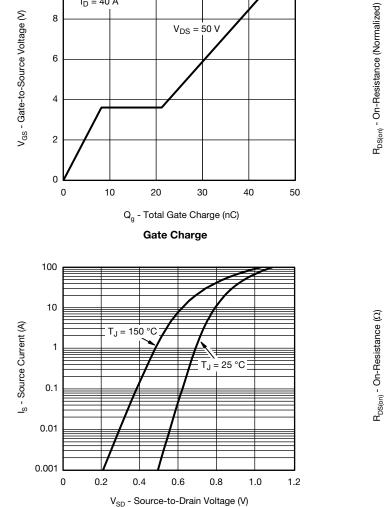
3

Document Number: 69064

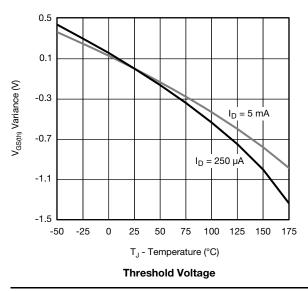
For technical questions, contact: <u>automostechsupport@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

 $I_D = 40 \text{ Å}$ 2.1

2.5



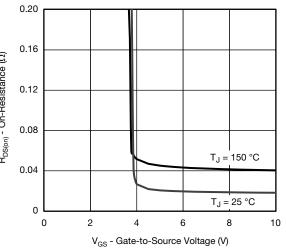
Source Drain Diode Forward Voltage



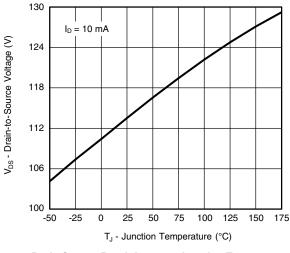
1.7 1.3 0.9 0.5 -25 0 50 75 175 -50 25 100 125 150

T<sub>.1</sub> - Junction Temperature (°C)

**On-Resistance vs. Junction Temperature** 



**On-Resistance vs. Gate-to-Source Voltage** 



Drain Source Breakdown vs. Junction Temperature

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V<sub>GS</sub> = 10 V

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TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

 $V_{DS} = 50 V$ 

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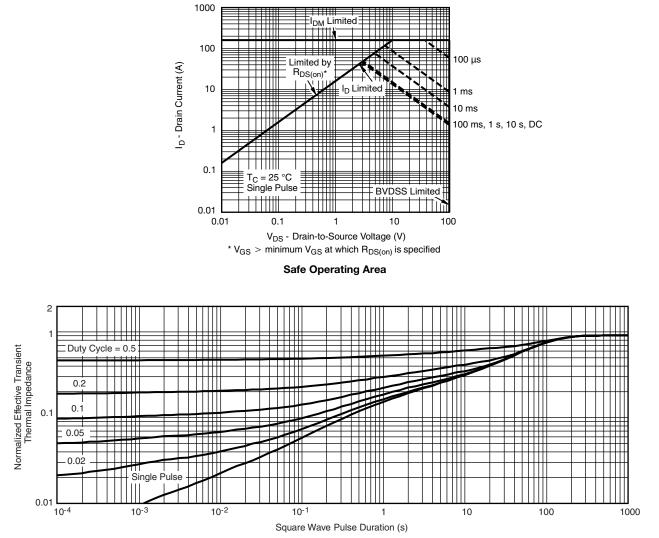
6

 $I_D = 40$  A



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#### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



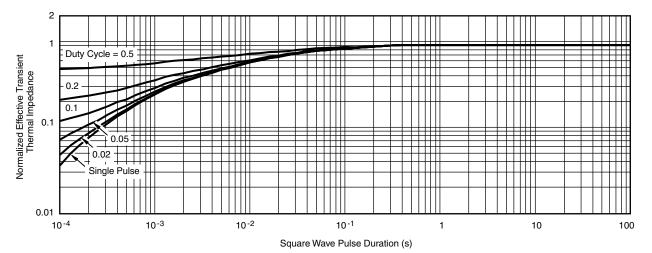
Normalized Thermal Transient Impedance, Junction-to-Ambient



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#### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

S15-1873-Rev. E, 10-Aug-15

- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

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<sup>•</sup> The characteristics shown in the two graphs



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REVISION	HISTORY <sup>a</sup>	
REVISION	DATE	DESCRIPTION OF CHANGE
E	04-Aug-15	Revised R <sub>g</sub> minimum limit

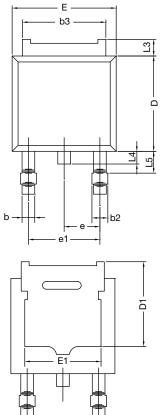
Note

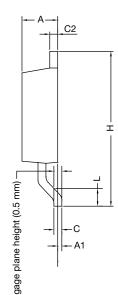
a. As of April 2014





**TO-252AA Case Outline** 





	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
А	2.18	2.38	0.086	0.094
A1	-	0.127	-	0.005
b	0.64	0.88	0.025	0.035
b2	0.76	1.14	0.030	0.045
b3	4.95	5.46	0.195	0.215
С	0.46	0.61	0.018	0.024
C2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	4.10	-	0.161	-
E	6.35	6.73	0.250	0.265
E1	4.32	-	0.170	-
Н	9.40	10.41	0.370	0.410
е	2.28	2.28 BSC		BSC
e1	4.56 BSC		0.180 BSC	
L	1.40	1.78	0.055	0.070
L3	0.89	1.27	0.035	0.050
L4	-	1.02	-	0.040
L5	1.01	1.52	0.040	0.060
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019				

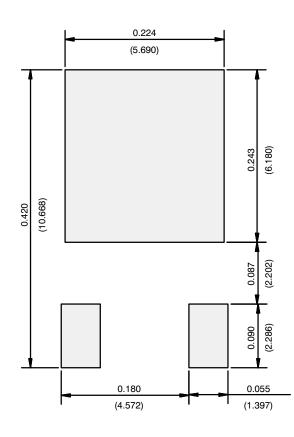
Note

• Dimension L3 is for reference only.



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#### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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